

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

re Application of

Masatoshi ANMA

Serial No.: 10/003,234

Filed: December 06, 2001

SEP 0 3 2002 4

Group Art Unit: 2826

Examiner: A. Sefer

SEMICONDUCTOR DEVICE HAVING ANTI-FUSE STRUCTURE

THE COMMISSIONER FOR PATENTS AND TRADEMARKS Washington, DC 20231

Dear Sir:

For:

Transmitted herewith is an Amendment in the above identified application.

No additional fee is required.

Applicant is entitled to small entity status under 37 CFR 1.27

Also attached:

The fee has been calculated as shown below:

	NO. OF CLAIMS	HIGHEST PREVIOUSLY PAID FOR	EXTRA CLAIMS	RATE	FEE
Total Claims	18	20	0	\$18.00 =	\$0.
Independent Claims	3	3	0	\$84.00 =	\$0.
		Multiple claims newly presented			\$0.
		Fee for extension of time			\$0.
					\$0.
		Total of Above Calculations			\$0.

Please charge my Deposit Account No. <u>500417</u> in the amount of \$0.00. An additional copy of this transmittal sheet is submitted herewith.

The Commissioner is hereby authorized to charge payment of any fees associated with this communication or credit any overpayment, to Deposit Account No. 500417, including any filing fees under 37 CFR 1.16 for presentation of extra claims and any patent application processing fees under 37 CFR 1.17.

Respectfully submitted,

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In re Application of

Anma MASATOSHI

Application No.: 10/003,234

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SEMICONDUCTOR DEVICE HAVING ANTI-FUSE STRUCTURE

AMENDMENT

Box Non-Fee Amendment The Commissioner for Patents and Trademarks Washington, DC 20231

Sir:

For:

The following Amendment and Remarks are submitted in response to the Office Action dated June 5, 2002. Please amend the above-identified application as follows:

IN THE CLAIMS:

Please amend claims 1, 6 and 15 as follows:

- 1. (Amended) A semiconductor device comprising:
- a substrate;
- a first interconnection formed on said substrate;
- a first dielectric film covering said first interconnection;

an opening section extending from a surface of the first dielectric film to said first interconnection, said opening section being formed in said first dielectric film;